

**AMENDMENTS TO THE CLAIMS:**

This listing of claims will replace all prior versions, and listings, of claims in the application:

**LISTING OF CLAIMS:**

1-13. (Canceled)

14. (Previously presented) An oxygen-free plasma etching gas formulation for removing an organic ARC on a metallic layer comprising CHF<sub>3</sub>, argon and HCl or BCl<sub>3</sub>, the gas formulation being free of SF<sub>6</sub>.

15-17. (Canceled)

18. (Previously presented) An oxygen-free plasma etching gas formulation for removing an organic ARC on a metallic layer comprising CHF<sub>3</sub>, argon and chlorine, the gas formulation being free of SF<sub>6</sub>, and a ratio of flow rates of CHF<sub>3</sub>:argon:chlorine in the formulation is 5 to 80 sccm:5 to 80 sccm:5 to 60 sccm.

19-20. (Canceled)

21. (Currently Amended) An oxygen-free plasma etching gas formulation for removing an organic ARC on a metallic layer comprising (i) more than one fluorine-containing compound, (ii) an inert carrier gas selected from the group consisting of ~~krypton~~, argon, neon, helium, and mixtures thereof, and (iii) chlorine, the gas formulation being free of SF<sub>6</sub>.

22-27. (Canceled)

28. (Previously presented) The gas formulation of Claim 14, which comprises HCl.

29. (Previously presented) The gas formulation of Claim 14, which comprises BCl<sub>3</sub>.

30. (Canceled)

31. (Previously presented) The gas formulation of Claim 21, wherein the inert carrier gas is argon.

32. (Previously presented) The gas formulation of Claim 21, wherein the inert carrier gas is neon.

33. (Previously presented) The gas formulation of Claim 21, wherein the inert carrier gas is helium.

34. (Canceled)

35. (Canceled)